

# MiniSKiiP® 3

### Sixpack

#### SKiiP 37AC12T4V1

#### Features\*

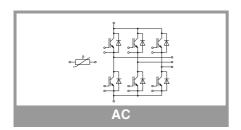
- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

#### **Typical Applications**

- Inverter up to 36 kVA
- Typical motor power 22 kW

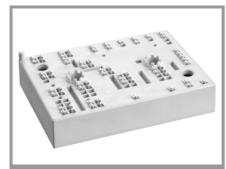
#### **Remarks**

- Max. case temperature limited to T<sub>C</sub>=125°C
- Product reliability results valid for T<sub>j</sub>≤150°C (recommended T<sub>j,op</sub>=-40...+150°C)
   MiniSKiiP "Technical Explanations"
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.



Absolute Maximum Ratings							
Symbol	Conditions		Values	Unit			
Inverter - IGBT							
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		1200	V			
Ic	$\lambda_{paste}$ =0.8 W/(mK) T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	90	Α			
		T <sub>s</sub> = 70 °C	73	Α			
I <sub>C</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	106	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	86	Α			
I <sub>Cnom</sub>			75	Α			
I <sub>CRM</sub>			225	Α			
V <sub>GES</sub>			-20 20	V			
t <sub>psc</sub>	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T <sub>j</sub> = 150 °C	10	μs			
Tj			-40 175	°C			
Inverse - D	Diode						
$V_{RRM}$	T <sub>j</sub> = 25 °C		1200	V			
l <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	83	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	66	Α			
l <sub>F</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	95	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	76	Α			
I <sub>FRM</sub>			150	Α			
I <sub>FSM</sub>	$t_p = 10 \text{ ms, sin } 180^\circ$	°, T <sub>j</sub> = 150 °C	430	Α			
Tj			-40 175	°C			
Module							
I <sub>t(RMS)</sub>	T <sub>terminal</sub> = 80 °C, 20	A per spring	160	Α			
T <sub>stg</sub>	module without TIM	1	-40 125	°C			
V <sub>isol</sub>	AC sinus 50 Hz, t =	: 1 min	2500	V			

Characteristics							
Symbol	Conditions		min.	typ.	max.	Unit	
Inverter - IGBT							
V <sub>CE(sat)</sub>	$V_{CE(sat)}$ $I_C = 75 \text{ A}$ $V_{GE} = 15 \text{ V}$ chiplevel	T <sub>j</sub> = 25 °C		1.85	2.10	V	
		T <sub>j</sub> = 150 °C		2.25	2.45	V	
V <sub>CE0</sub>	chiplevel	T <sub>j</sub> = 25 °C		0.80	0.90	V	
		T <sub>j</sub> = 150 °C		0.70	0.80	V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25 °C		14	16	mΩ	
	chiplevel	T <sub>j</sub> = 150 °C		21	22	mΩ	
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 3 \text{ m}$	A	5	5.8	6.5	V	
I <sub>CES</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 12$			1	mA		
C <sub>ies</sub>	V 05.V	f = 1 MHz		4.40		nF	
Coes	V <sub>CE</sub> = 25 V V <sub>GE</sub> = 0 V	f = 1 MHz		0.29		nF	
C <sub>res</sub>		f = 1 MHz		0.24		nF	
$Q_{G}$	V <sub>GE</sub> = - 8 V+ 15 V			425		nC	
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C			10		Ω	
t <sub>d(on)</sub>	V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		145		ns	
t <sub>r</sub>	I <sub>C</sub> = 75 A	T <sub>j</sub> = 150 °C		45		ns	
Eon	$\begin{aligned} R_{G \text{ on}} &= 1 \ \Omega \\ R_{G \text{ off}} &= 1 \ \Omega \\ \text{di/dt}_{\text{on}} &= 1560 \ \text{A/}\mu\text{s} \\ \text{di/dt}_{\text{off}} &= 1180 \ \text{A/}\mu\text{s} \end{aligned}$	T <sub>j</sub> = 150 °C		11.5		mJ	
t <sub>d(off)</sub>		T <sub>j</sub> = 150 °C		350		ns	
t <sub>f</sub>				65		ns	
E <sub>off</sub>	V <sub>GE</sub> = +15/-15 V	T <sub>j</sub> = 150 °C		6.8		mJ	
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =0.8 W/(mK)			0.58		K/W	
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =2.5 W/(mK)			0.44		K/W	



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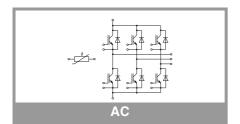
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Characteristics									
Symbol	Conditions	min.	typ.	max.	Unit				
Inverse - Diode									
$V_F = V_{EC}$	$V_F = V_{EC}$ $V_{GE} = 0 V$ $V_{GE} = 0 V$ $V_{GE} = 0 V$	T <sub>j</sub> = 25 °C		2.17	2.49	V			
		T <sub>j</sub> = 150 °C		2.11	2.42	V			
V <sub>F0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V			
		T <sub>j</sub> = 150 °C		0.90	1.10	V			
r <sub>F</sub>	- chiplevel	T <sub>j</sub> = 25 °C		12	13	$m\Omega$			
		T <sub>j</sub> = 150 °C		16	18	$m\Omega$			
I <sub>RRM</sub>	$\begin{aligned} I_F &= 75 \text{ A} \\ \text{di/dt}_{\text{off}} &= 2440 \text{ A/}\mu\text{s} \\ \text{V}_{GE} &= +15/-15 \text{ V} \\ \text{V}_{CC} &= 600 \text{ V} \end{aligned}$	T <sub>j</sub> = 150 °C		99		Α			
Q <sub>rr</sub>		T <sub>j</sub> = 150 °C		13.3		μC			
E <sub>rr</sub>		T <sub>j</sub> = 150 °C		5.5		mJ			
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0.8 W/(mK)			0.75		K/W			
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =2.5 W/(mK)			0.61		K/W			
Module									
L <sub>CE</sub>				-		nH			
Ms	to heat sink		2		2.5	Nm			
w				82		g			
Temperature Sensor									
R <sub>100</sub>	T <sub>r</sub> =100°C (R <sub>25</sub> =1000Ω)			1670 ± 3%		Ω			
R <sub>(T)</sub>	$R_{(T)}=1000\Omega[1+A(T-25^{\circ}C)+B(T-25^{\circ}C)^{2}]$ , A = 7.635*10 <sup>-3°</sup> C <sup>-1</sup> , B = 1.731*10 <sup>-5°</sup> C <sup>-2</sup>								



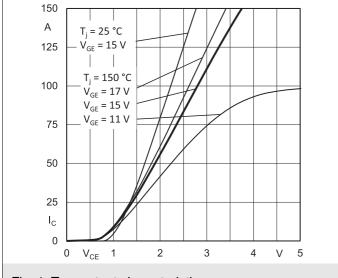


Fig. 1: Typ. output characteristic

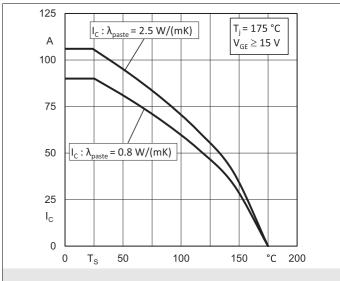


Fig. 2: Rated current vs. temperature  $I_C = f(T_S)$ 

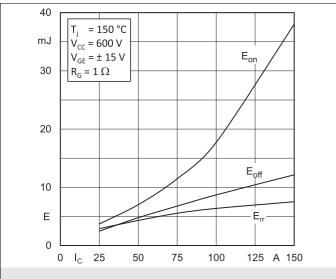


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$ 

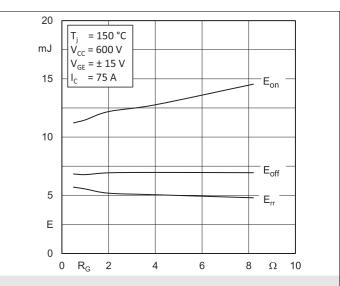


Fig. 4: Typ. turn-on /-off energy = f (R<sub>G</sub>)

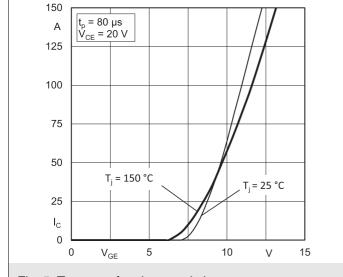


Fig. 5: Typ. transfer characteristic

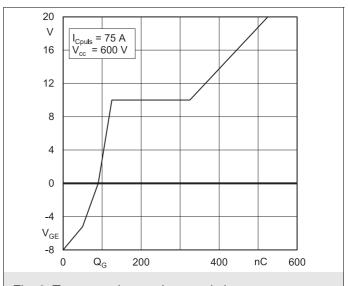


Fig. 6: Typ. gate charge characteristic

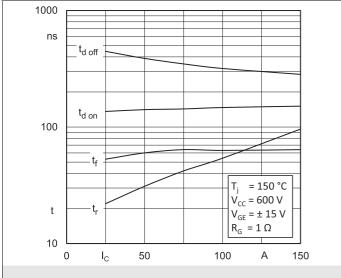


Fig. 7: Typ. switching times vs.  $I_C$ 

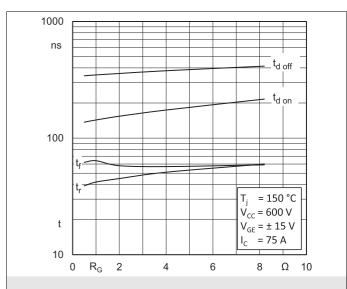


Fig. 8: Typ. switching times vs. gate resistor  $R_{\text{G}}$ 

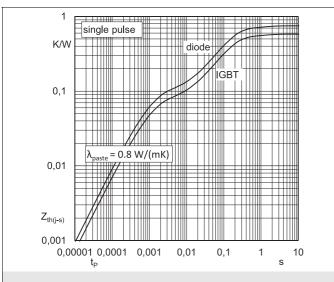


Fig. 9: Typ. transient thermal impedance

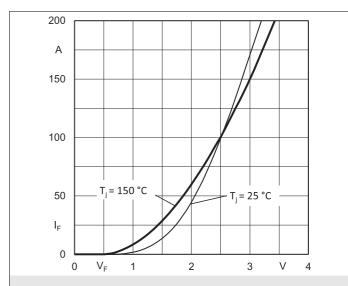


Fig. 10: Typ. CAL diode forward characteristic

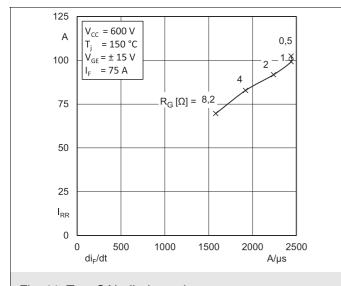


Fig. 11: Typ. CAL diode peak reverse recovery current

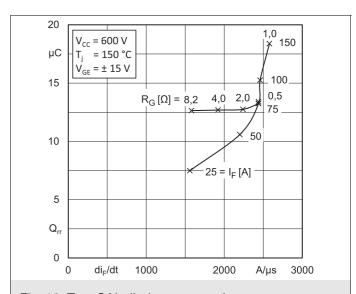
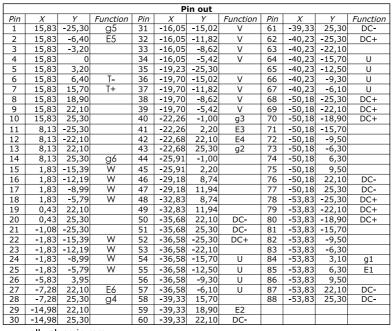
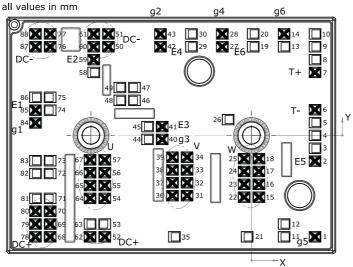
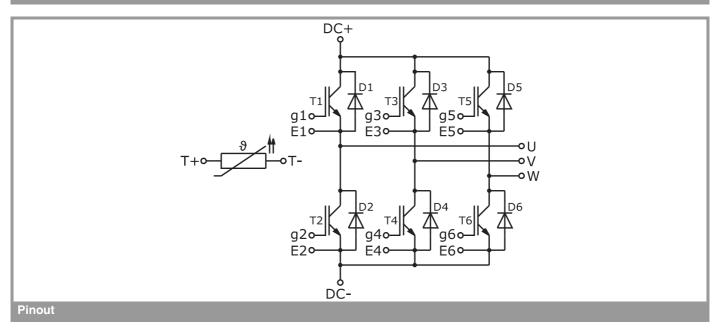


Fig. 12: Typ. CAL diode recovery charge





**Pinout and Dimensions** 



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

#### \*IMPORTANT INFORMATION AND WARNINGS

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